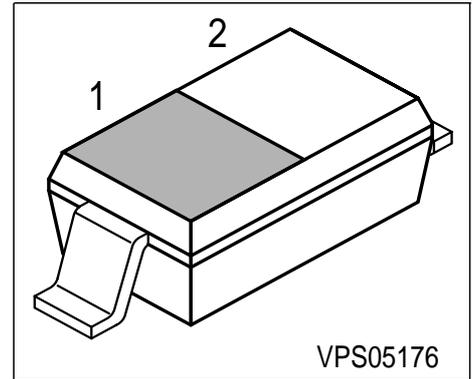


Silicon Schottky Diode

- Low barrier diode for detectors up to GHz frequencies



ESD: Electrostatic discharge sensitive device, observe handling precaution!

Type	Marking	Pin Configuration		Package
BAT62-03W	L	1 = C	2 = A	SOD323

Maximum Ratings

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	40	V
Forward current	I_F	40	mA
Total power dissipation, $T_S \leq 85\text{ °C}$	P_{tot}	150	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 ... 150	

Thermal Resistance

Junction - soldering point ¹⁾	R_{thJS}	≤ 810	K/W
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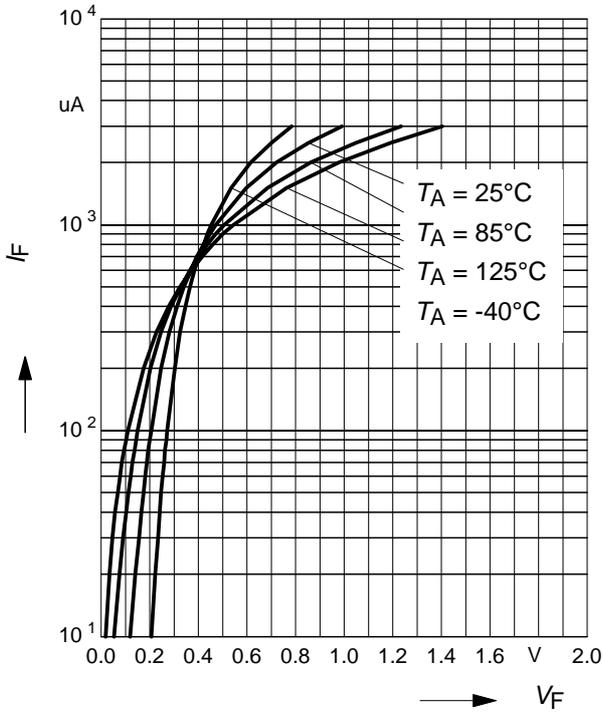
¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC characteristics					
Reverse current $V_R = 40\text{ V}$	I_R	-	-	10	μA
Forward voltage $I_F = 2\text{ mA}$	V_F	-	0.58	1	V
AC characteristics					
Diode capacitance $V_R = 0\text{ V}, f = 1\text{ MHz}$	C_T	-	0.35	0.6	pF
Case capacitance $f = 1\text{ MHz}$	C_C	-	0.1	-	
Differential resistance $V_R = 0, f = 10\text{ kHz}$	R_0	-	225	-	k Ω
Series inductance	L_s	-	1.8	-	nH

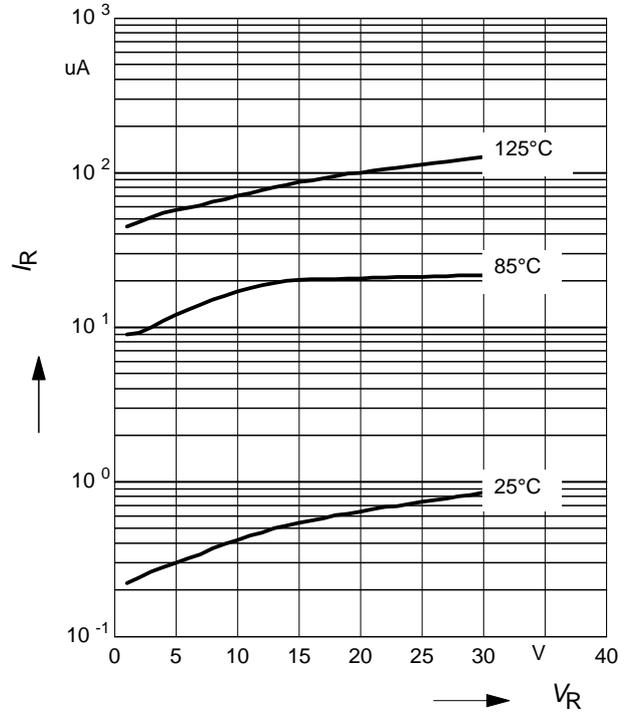
Forward current $I_F = f(V_F)$

$T_A = \text{parameter}$



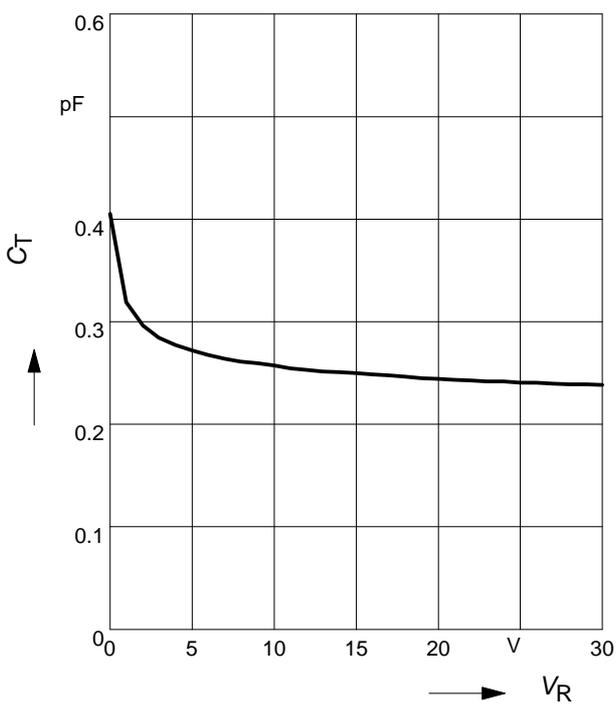
Leakage current $I_R = f(V_R)$

$T_A = \text{Parameter}$



Diode capacitance $C_T = f(V_R)$

$f = 1\text{MHz}$



Rectifier voltage $V_A = f(V_E)$

$f = 900\text{ MHz}$

$R_L = \text{parameter in } \Omega$

